Czeslaw Skierbiszewski

List of Publications by Year in Descending Order

222 papers	3,101 citations	27 h-index	48 g-index
250 ext. papers	3,416 ext. citations	2.3 avg, IF	4.53 L-index

#	Paper	IF	Citations
222	GaN-based bipolar cascade lasers with 25 nm wide quantum wells. *Optical and Quantum Electronics*, **2022**, 54, 1	2.4	0
221	Electrically pumped blue laser diodes with nanoporous bottom cladding.. *Optics Express*, **2022**, 30, 10709-10722	3.3	2
220	Bottom tunnel junction-based blue LED with a thin Ge-doped current spreading layer. *Applied Physics Letters*, **2022**, 120, 171104	3.4	0
219	Electrochemical etching of p-type GaN using a tunnel junction for efficient hole injection. *Acta Materialia*, **2022**, 118018	8.4	0
218	Material Gain in Polar GaInN and AlGaN Quantum Wells: How to Overcome the "Dead" Width for Light Emitters in These QW Systems?. *IEEE Journal of Selected Topics in Quantum Electronics*, **2021**, 1-1	3.8	0
217	Tunnel Junctions with a Doped (In,Ga)N Quantum Well for Vertical Integration of III-Nitride Optoelectronic Devices. *Physical Review Applied*, **2021**, 15,	4.3	6
216	Composition Inhomogeneity in Nonpolar (101 0) and Semipolar (202 1) InAlN Layers Grown by Plasma-Assisted Molecular Beam Epitaxy. *Crystal Growth and Design*, **2021**, 21, 5223-5230	3.5	1
215	Optical properties of N-polar GaN: The possible role of nitrogen vacancy-related defects. *Applied Surface Science*, **2021**, 566, 150734	6.7	1
214	Quantum-confined Stark effect and mechanisms of its screening in InGaN/GaN light-emitting diodes with a tunnel junction. *Optics Express*, **2021**, 29, 1824-1837	3.3	7
213	Dependence of InGaN Quantum Well Thickness on the Nature of Optical Transitions in LEDs.. *Materials*, **2021**, 15,	3.5	2
212	Vertical Integration of Nitride Laser Diodes and Light Emitting Diodes by Tunnel Junctions. *Electronics (Switzerland)*, **2020**, 9, 1481	2.6	8
211	Hydrostatic pressure dependence of indirect and direct excitons in InGaN/GaN quantum wells. *Physical Review B*, **2020**, 101,	3.3	2
210	Inhomogeneous broadening of optical transitions observed in photoluminescence and modulated reflectance of polar and non-polar InGaN quantum wells. *Journal of Applied Physics*, **2020**, 127, 035702	2.5	1
209	Revealing inhomogeneous Si incorporation into GaN at the nanometer scale by electrochemical etching. *Nanoscale*, **2020**, 12, 6137-6143	7.7	4
208	Stacking faults in plastically relaxed InGaN epilayers. *Semiconductor Science and Technology*, **2020**, 35, 034003	1.8	3
207	Monolithically p-down nitride laser diodes and LEDs obtained by MBE using buried tunnel junction design **2020**,		2
206	Anomalous photocurrent in wide InGaN quantum wells. *Optics Express*, **2020**, 28, 4717-4725	3.3	3

205	Enhanced injection efficiency and light output in bottom tunnel-junction light-emitting diodes. *Optics Express*, **2020**, 28, 4489-4500	3.3	12
204	InGaN blue light emitting micro-diodes with current path defined by tunnel junction. *Optics Letters*, **2020**, 45, 4332-4335	3	1
203	Distributed-feedback blue laser diode utilizing a tunnel junction grown by plasma-assisted molecular beam epitaxy. *Optics Express*, **2020**, 28, 35321-35329	3.3	3
202	Nitride light-emitting diodes for cryogenic temperatures. *Optics Express*, **2020**, 28, 30299-30308	3.3	3
201	Role of high nitrogen flux in InAlN growth by plasma-assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2020**, 544, 125720	1.6	2
200	Nitride LEDs and Lasers with Buried Tunnel Junctions. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 015018	2	5
199	Laser Diodes Grown by Molecular Beam Epitaxy **2020**, 301-332		
198	Optical properties of III-nitride laser diodes with wide InGaN quantum wells. *Applied Physics Express*, **2019**, 12, 072003	2.4	7
197	Unusual step meandering due to Ehrlich-Schwoebel barrier in GaN epitaxy on the N-polar surface. *Applied Surface Science*, **2019**, 484, 771-780	6.7	12
196	Nitrogen-rich growth for device quality N-polar InGaN/GaN quantum wells by plasma-assisted MBE. *Journal of Crystal Growth*, **2019**, 512, 208-212	1.6	4
195	MBE of III-Nitride Heterostructures for Optoelectronic Devices **2019**, 191-209		
194	Impact of the substrate lattice constant on the emission properties of InGaN/GaN short-period superlattices grown by plasma assisted MBE. *Superlattices and Microstructures*, **2019**, 133, 106209	2.8	3
193	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. *ACS Photonics*, **2019**, 6, 1963-1971	6.3	16
192	Stack of two III-nitride laser diodes interconnected by a tunnel junction. *Optics Express*, **2019**, 27, 5784-5791	3.3	22
191	Influence of Electron Blocking Layer on Properties of InGaN-Based Laser Diodes Grown by Plasma-Assisted Molecular Beam Epitaxy. *Acta Physica Polonica A*, **2019**, 136, 593-597	0.6	1
190	Extremely long lifetime of III-nitride laser diodes grown by plasma assisted molecular beam epitaxy. *Materials Science in Semiconductor Processing*, **2019**, 91, 387-391	4.3	9
189	Depletion Layer Built-In Field at ($1\bar{1}00$), (0001), and ($000\bar{1}$) GaN/Water Junction and Its Role in Semiconductor Nanowire Water Splitting. *Advanced Materials Interfaces*, **2019**, 6, 1801497	4.6	
188	Sensitivity of N-polar GaN surface barrier to ambient gases. *Sensors and Actuators B: Chemical*, **2019**, 281, 561-567	8.5	5

187	Hydrogen diffusion in GaN:Mg and GaN:Si. *Journal of Alloys and Compounds*, **2018**, 747, 354-358	5.7	18
186	Luminescent N-polar (In,Ga)N/GaN quantum wells achieved by plasma-assisted molecular beam epitaxy at temperatures exceeding 700 ℃. *Applied Physics Letters*, **2018**, 112, 022102	3.4	8
185	Dependence of indium content in monolayer-thick InGaN quantum wells on growth temperature in InxGa1-xN/In0.02Ga0.98N superlattices. *Journal of Applied Physics*, **2018**, 124, 065701	2.5	9
184	Growth rate independence of Mg doping in GaN grown by plasma-assisted MBE. *Journal of Crystal Growth*, **2018**, 482, 56-60	1.6	6
183	Switching of exciton character in double InGaN/GaN quantum wells. *Physical Review B*, **2018**, 98,	3.3	8
182	True-blue laser diodes with tunnel junctions grown monolithically by plasma-assisted molecular beam epitaxy. *Applied Physics Express*, **2018**, 11, 034103	2.4	34
181	Miscut dependent surface evolution in the process of N-polar . *Journal of Crystal Growth*, **2017**, 457, 38-456		8
180	Comparative study of semipolar(202□1), nonpolar(101□0)and polar(0001)InGaN multi-quantum well structures grown under N- and In-excess by plasma assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2017**, 465, 43-47	1.6	5
179	Indium incorporation in semipolar (202 1) and nonpolar (101 0) InGaN grown by plasma assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2017**, 459, 129-134	1.6	15
178	Transparency of Semi-Insulating, n-Type, and p-Type Ammonothermal GaN Substrates in the Near-Infrared, Mid-Infrared, and THz Spectral Range. *Crystals*, **2017**, 7, 187	2.3	9
177	Bandgap behavior of InGaN/GaN short period superlattices grown by metal-organic vapor phase epitaxy. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600710	1.3	7
176	Influence of the growth method on degradation of InGaN laser diodes. *Applied Physics Express*, **2017**, 10, 091001	2.4	8
175	S-shaped negative differential resistance in III-Nitride blue quantum-well laser diodes grown by plasma-assisted MBE **2017**,		1
174	Aluminum-free nitride laser diodes: waveguiding, electrical and degradation properties. *Optics Express*, **2017**, 25, 33113	3.3	5
173	Elimination of leakage of optical modes to GaN substrate in nitride laser diodes using a thick InGaN waveguide. *Applied Physics Express*, **2016**, 9, 092103	2.4	21
172	Lateral Schottky barrier diodes based on GaN/AlGaN 2DEG for sub-THz detection **2016**,		2
171	Surface potential barrier inm-plane GaN studied by contactless electroreflectance. *Applied Physics Express*, **2016**, 9, 021002	2.4	2
170	Sensitivity of Fermi level position at Ga-polar, N-polar, and nonpolarm-plane GaN surfaces to vacuum and air ambient. *Japanese Journal of Applied Physics*, **2016**, 55, 05FA08	1.4	6

169	A Model of Radiative Recombination in (In,Al,Ga)N/GaN Structures with Significant Potential Fluctuations. *Acta Physica Polonica A*, **2016**, 130, 1209-1212	0.6	0
168	Terahertz 3D printed diffractive lens matrices for field-effect transistor detector focal plane arrays. *Optics Express*, **2016**, 24, 20119-31	3.3	15
167	MBE grown GaN/AlGaN lateral Schottky barrier diodes for high frequency applications. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2016**, 34, 02L118	1.3	9
166	Surface Leakage Currents in SiN and Al 2 O 3 Passivated AlGaN/GaN High Electron Mobility Transistors. *Chinese Physics Letters*, **2016**, 33, 067201	1.8	1
165	Investigation of interface abruptness and In content in (In,Ga)N/GaN superlattices. *Journal of Applied Physics*, **2016**, 120, 125307	2.5	13
164	Strain relaxation in semipolar (202□1) InGaN grown by plasma assisted molecular beam epitaxy. *Journal of Applied Physics*, **2016**, 119, 185701	2.5	5
163	Electric field dynamics in nitride structures containing quaternary alloy (Al, In, Ga)N. *Journal of Applied Physics*, **2016**, 120, 015702	2.5	2
162	Low frequency noise in two-dimensional lateral GaN/AlGaN Schottky diodes. *Applied Physics Letters*, **2016**, 109, 033502	3.4	5
161	HVPE-GaN growth on GaN-based Advanced Substrates by Smart Cut□*Journal of Crystal Growth*, **2016**, 456, 73-79	1.6	7
160	Comparison of the Luminous Efficiencies of Ga- and N-Polar InxGa1□xN/InyGa1□yN Quantum Wells Grown by Plasma-Assisted Molecular Beam Epitaxy. *Physical Review Applied*, **2016**, 6,	4.3	11
159	High power nitride laser diodes grown by plasma assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2015**, 425, 398-400	1.6	13
158	Photoluminescence characterization of InGaN/InGaN quantum wells grown by plasma-assisted molecular beam epitaxy: Impact of nitrogen and galium fluxes. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 983-988	1.3	1
157	Enhancement of optical confinement factor by InGaN waveguide in blue laser diodes grown by plasma-assisted molecular beam epitaxy. *Applied Physics Express*, **2015**, 8, 032103	2.4	23
156	AlGaN/GaN HEMT□ photoresponse to high intensity THz radiation. *Opto-electronics Review*, **2015**, 23,	2.4	7
155	Theoretical and experimental studies of electric field distribution in N-polar GaN/AlGaN/GaN heterostructures. *Applied Physics Letters*, **2015**, 107, 262107	3.4	8
154	Influence of quantum well inhomogeneities on absorption, spontaneous emission, photoluminescence decay time, and lasing in polar InGaN quantum wells emitting in the blue-green spectral region. *Applied Physics A: Materials Science and Processing*, **2014**, 115, 1015-1023	2.6	6
153	Separating strain from composition in unit cell parameter maps obtained from aberration corrected high resolution transmission electron microscopy imaging. *Journal of Applied Physics*, **2014**, 115, 033113	2.5	9
152	True-blue laser diodes grown by plasma-assisted MBE on bulk GaN substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 666-669		1

151	Nitride-based laser diodes grown by plasma-assisted molecular beam epitaxy. *Journal Physics D: Applied Physics*, **2014**, 47, 073001	3	39
150	Semipolar (202□1) GaN laser diodes operating at 388 nm grown by plasma-assisted molecular beam epitaxy. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2014**, 32, 02C115	1.3	1
149	AlGaN cladding-free 482 nm continuous wave nitride laser diodes grown by plasma-assisted molecular beam epitaxy. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2014**, 32, 02C112	1.3	
148	Cyan laser diode grown by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2014**, 104, 023503	3.4	8
147	Nitride-based laser diodes and superluminescent diodes. *Photonics Letters of Poland*, **2014**, 6,	2.1	2
146	Contactless electroreflectance studies of surface potential barrier for N- and Ga-face epilayers grown by molecular beam epitaxy. *Applied Physics Letters*, **2013**, 103, 052107	3.4	17
145	Determination of gain in AlGaN cladding free nitride laser diodes. *Applied Physics Letters*, **2013**, 103, 061102	3.4	12
144	Step-flow growth mode instability of N-polar GaN under N-excess. *Applied Physics Letters*, **2013**, 103, 071601	3.4	12
143	Growth mechanisms in semipolar and nonpolar m-plane AlGaN/GaN structures grown by PAMBE under N-rich conditions. *Journal of Crystal Growth*, **2013**, 377, 184-191	1.6	20
142	Ultraviolet light-emitting diodes grown by plasma-assisted molecular beam epitaxy on semipolar GaN (202□1) substrates. *Applied Physics Letters*, **2013**, 102, 111107	3.4	9
141	Nonequivalent atomic step edges□Role of gallium and nitrogen atoms in the growth of InGaN layers. *Journal of Crystal Growth*, **2013**, 367, 115-121	1.6	34
140	Ultraviolet laser diodes grown on semipolar (202□1) GaN substrates by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2013**, 102, 251101	3.4	12
139	MBE fabrication of III-N-based laser diodes and its development to industrial system. *Journal of Crystal Growth*, **2013**, 378, 278-282	1.6	13
138	Surface properties of c-plane GaN grown by plasma-assisted molecular beam epitaxy. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2013**, 31, 03C112	1.3	10
137	Investigation on the origin of luminescence quenching in N-polar (In,Ga)N multiple quantum wells. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2013**, 31, 03C130	1.3	11
136	Role of Nonequivalent Atomic Step Edges in the Growth of InGaN by Plasma-Assisted Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2013**, 52, 08JE02	1.4	4
135	Contactless electroreflectance studies of Fermi level position on c-plane GaN surface grown by molecular beam epitaxy and metalorganic vapor phase epitaxy. *Applied Physics Letters*, **2012**, 100, 181603	3.4	29
134	Electromodulation spectroscopy of optical transitions and electric field distribution in GaN/AlGaN/GaN transistor heterostructures with various AlGaN layer thicknesses. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 1092-1095		2

133	True-Blue Nitride Laser Diodes Grown by Plasma-Assisted Molecular Beam Epitaxy. *Applied Physics Express*, **2012**, 5, 112103	2.4	16
132	AlGaN-Free Laser Diodes by Plasma-Assisted Molecular Beam Epitaxy. *Applied Physics Express*, **2012**, 5, 022104	2.4	15
131	InGaN laser diodes operating at 450–460 nm grown by rf-plasma MBEa). *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2012**, 30, 02B102	1.3	15
130	Nitride-Based Light-Emitting Diodes and Nitride-Based Laser Diodes by Plasma-Assisted Molecular Beam Epitaxy **2012**, 355-385		1
129	Waveguide Design for Long Wavelength InGaN Based Laser Diodes. *Acta Physica Polonica A*, **2012**, 122, 1031-1033	0.6	7
128	Electrostatic Gates for GaN/AlGaN Quantum Point Contacts. *Acta Physica Polonica A*, **2012**, 122, 1026-1028	0.6	
127	The surface boundary conditions in GaN/AlGaN/GaN transistor heterostructures. *Applied Physics Letters*, **2011**, 98, 231902	3.4	27
126	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. *Journal of Applied Physics*, **2011**, 110, 063110	2.5	39
125	Surface and in-depth characterization of InGaN compounds synthesized by plasma-assisted molecular beam epitaxy. *Journal of Alloys and Compounds*, **2011**, 509, 9565-9571	5.7	14
124	Theoretical simulations of radiative recombination time in polar InGaN quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2273-2275		3
123	Broadening of interband transitions in InGaN quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2282-2284		3
122	Growth mechanism of InGaN by plasma assisted molecular beam epitaxy. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2011**, 29, 03C136	1.3	23
121	Electron spin resonance and Rashba field in GaN-based materials. *Physica B: Condensed Matter*, **2011**, 406, 2548-2554	2.8	8
120	High quality m-plane GaN grown under nitrogen-rich conditions by plasma assisted molecular beam epitaxya). *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2011**, 29, 03C135	1.3	9
119	Mismatch relaxation by stacking fault formation of AlN islands in AlGaN/GaN structures on m-plane GaN substrates. *Applied Physics Letters*, **2011**, 99, 061901	3.4	12
118	Step-flow anisotropy of the m-plane GaN (11–00) grown under nitrogen-rich conditions by plasma-assisted molecular beam epitaxy. *Physical Review B*, **2011**, 83,	3.3	17
117	InAlGaN laser diodes grown by plasma assisted molecular beam epitaxy. *Lithuanian Journal of Physics*, **2011**, 51, 276-282	1.1	0
116	Broadening of intersubband transitions in InGaN/AlInN multiquantum wells. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2010**, 28, C3B17-C3B21	1.3	1

115	AlGaN/GaN high electron mobility transistors as a voltage-tunable room temperature terahertz sources. *Journal of Applied Physics*, **2010**, 107, 024504	2.5	103
114	Broadening of intersubband and interband transitions in InGaN/AlInN multi-quantum wells. *Journal Physics D: Applied Physics*, **2010**, 43, 195101	3	1
113	TEM investigation of a processed InGaN based laser grown by PAMBE on bulk GaN substrate. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 1325-1328		2
112	Contactless electroreflectance of InGaN layers with indium content 36%: The surface band bending, band gap bowing, and Stokes shift issues. *Journal of Applied Physics*, **2009**, 106, 113517	2.5	26
111	Doping-Induced Contrast in the Refractive Index for GaInN/GaN Structures at Telecommunication Wavelengths. *Applied Physics Express*, **2009**, 2, 111001	2.4	5
110	InGaN light emitting diodes for 415 nm 520 nm spectral range by plasma assisted MBE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S917-S920		29
109	Contactless electroreflectance of GaInN/AlInN multi quantum wells: The issue of broadening of optical transitions. *Microelectronics Journal*, **2009**, 40, 392-395	1.8	3
108	Electromodulation spectroscopy of the ground and excited state transitions in GaInN/AlInN multi-quantum wells. *Microelectronics Journal*, **2009**, 40, 805-808	1.8	
107	Nitride-based laser diodes by plasma-assisted MBE rom violet to green emission. *Journal of Crystal Growth*, **2009**, 311, 1632-1639	1.6	43
106	Tunable room temperature terahertz sources based on two dimensional plasma instability in GaN HEMTs. *Journal of Physics: Conference Series*, **2009**, 193, 012072	0.3	
105	Near IR Refractive Index for GaInN Heavily Doped with Silicon. *Acta Physica Polonica A*, **2009**, 116, 936-938	0.6	
104	Blue Laser Diodes by Low Temperature Plasma Assisted MBE. *Solid State Phenomena*, **2008**, 140, 17-26	0.4	2
103	Contactless electroreflectance spectroscopy of inter- and intersub-band transitions in AlInN/GaInN quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 503-507		3
102	Optically pumped lasing of GaN/AlGaN structures grown along a non-polar crystallographic direction. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 2173-2175		
101	Computer-assisted analysis of TEM diffraction contrast images of (In,Ga)N/GaN nanostructures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 3732-3735		1
100	TEM investigations of (In,Ga)N/GaN quantum structures. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 2573-2576	1.6	
99	Growth of InGaN and InGaN/InGaN quantum wells by plasma-assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2008**, 310, 3983-3986	1.6	32
98	Enhancement of Intersubband Absorption in GaInN/AlInN Quantum Wells. *Acta Physica Polonica A*, **2008**, 114, 1093-1099	0.6	3

97	Experimental Studies of GaInNAs Conduction Band Structure **2008**, 123-161		
96	LASER DIODES GROWN ON BULK GALLIUM NITRIDE SUBSTRATES **2008**, 223-252		
95	Zero Field Spin Splitting in GaN/AlGaN Heterostructures Probed by the Weak Antilocalization. *Acta Physica Polonica A*, **2008**, 114, 1109-1113	0.6	
94	Properties of the Two-Dimensional Electron Gas Confined in GaN/AlGaN Interface Studied by Electron Spin Resonance. *AIP Conference Proceedings*, **2007**,	0	3
93	Role of dislocation-free GaN substrates in the growth of indium containing optoelectronic structures by plasma-assisted MBE. *Journal of Crystal Growth*, **2007**, 305, 346-354	1.6	18
92	Comparison of gain in group-III-nitride laser structures grown by metalorganic vapour phase epitaxy and plasma-assisted molecular beam epitaxy on bulk GaN substrates. *Semiconductor Science and Technology*, **2007**, 22, 736-741	1.8	3
91	Optically pumped GaN/AlGaN separate-confinement heterostructure laser grown along the (112□0) nonpolar direction. *Applied Physics Letters*, **2007**, 90, 081104	3.4	14
90	Plasmon-cyclotron resonance in two-dimensional electron gas confined at the GaN/AlxGa1−xN interface. *Physical Review B*, **2007**, 76,	3.3	12
89	Complete in-plane polarization anisotropy of the A exciton in unstrained A-plane GaN films. *Applied Physics Letters*, **2007**, 91, 141903	3.4	29
88	Mode dynamics of high power (InAl)GaN based laser diodes grown on bulk GaN substrate. *Journal of Applied Physics*, **2007**, 101, 083109	2.5	12
87	Influence of Electric Field on Recombination Dynamics of Quantum Confined Carriers. *Acta Physica Polonica A*, **2007**, 112, 243-247	0.6	4
86	Deep-Level Defects in MBE-Grown GaN-Based Laser Structure. *Acta Physica Polonica A*, **2007**, 112, 331-336	0.6	2
85	Optically Pumped Laser Action on Nitride Based Separate Confinement Heterostructures Grown along the (11□20) Crystallographic Direction. *Acta Physica Polonica A*, **2007**, 112, 467-472	0.6	
84	Electron-Electron Interaction Effects in Quantum Hall Regime of GaN/AlGaN Heterostructures. *Acta Physica Polonica A*, **2007**, 112, 269-273	0.6	
83	Growth of thin AlInN/GaInN quantum wells for applications to high-speed intersubband devices at telecommunication wavelengths. *Journal of Vacuum Science & Technology B*, **2006**, 24, 1505		24
82	60mW continuous-wave operation of InGaN laser diodes made by plasma-assisted molecular-beam epitaxy. *Applied Physics Letters*, **2006**, 88, 221108	3.4	45
81	Energy difference between electron subbands in AlInN/GaInN quantum wells studied by contactless electroreflectance spectroscopy. *Applied Physics Letters*, **2006**, 89, 251908	3.4	13
80	Negative differential resistance in dislocation-free GaN/AlGaN double-barrier diodes grown on bulk GaN. *Applied Physics Letters*, **2006**, 88, 172106	3.4	90

79	Growth and characterization of AlInN/GaInN quantum wells for high-speed intersubband devices at telecommunication wavelengths **2006**,		3
78	Barrier-to-well carrier dynamics of InGaN/GaN multi-quantum-wells grown by plasma assisted MBE on bulk GaN substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1962-1965		1
77	Role of band potential roughness on the luminescence properties of InGaN quantum wells grown by MBE on bulk GaN substrates. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1614-1618	1.3	6
76	Crack Free GaInN/AlInN Multiple Quantum Wells Grown on GaN with Strong Intersubband Absorption at 1.55□m. *Acta Physica Polonica A*, **2006**, 110, 175-181	0.6	3
75	High Power Continuous Wave Blue InAlGaN Laser Diodes Made by Plasma Assisted MBE. *Acta Physica Polonica A*, **2006**, 110, 345-351	0.6	1
74	Effective g* factor in the diluted nitrides Ga1−□InyNxAs1−□. *Physical Review B*, **2005**, 71,	3.3	11
73	High power blue□violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. *Semiconductor Science and Technology*, **2005**, 20, 809-813	1.8	30
72	High mobility two-dimensional electron gas in AlGaN□GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy. *Applied Physics Letters*, **2005**, 86, 102106	3.4	52
71	Control of Mg doping of GaN in RF-plasma molecular beam epitaxy. *Journal of Crystal Growth*, **2005**, 278, 443-448	1.6	21
70	Influence of dislocation and ionized impurity scattering on the electron mobility in GaN/AlGaN heterostructures. *Journal of Crystal Growth*, **2005**, 281, 194-201	1.6	6
69	High magnetic field studies of AlGaN/GaN heterostructures grown on bulk GaN. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1355-1359		2
68	High temperature electrical investigations of (Al,Ga)N/GaN heterostructures □Hall sensor applications. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1438-1443		12
67	Anomalous behaviour of the photoluminescence from GaN/AlGaN quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1010-1013		1
66	Blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. *Applied Physics Letters*, **2005**, 86, 011114	3.4	62
65	Free and bound excitons in GaN□AlGaN homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (112□0) direction. *Applied Physics Letters*, **2005**, 86, 162112	3.4	25
64	From High Electron Mobility GaN/AlGaN Heterostructures to Blue-Violet InGaN Laser Diodes. Perspectives of MBE for Nitride Optoelectronics. *Acta Physica Polonica A*, **2005**, 108, 635-651	0.6	6
63	Stimulated Emission from the MBE Grown Homoepitaxial InGaN Based Multiple Quantum Wells Structures. *Acta Physica Polonica A*, **2005**, 107, 225-229	0.6	
62	Low dislocation density, high power InGaN laser diodes. *MRS Internet Journal of Nitride Semiconductor Research*, **2004**, 9, 1		9

61	Zeeman splitting in GaInNAs. *Journal of Physics Condensed Matter*, **2004**, 16, S3319-S3331	1.8	6
60	Growth optimisation of the GaN layers and GaN/AlGaN heterojunctions on bulk GaN substrates using plasma-assisted molecular beam epitaxy. *Physica Status Solidi A*, **2004**, 201, 320-323		35
59	GaN based light emitters fabricated on bulk GaN substrates. New class of low dislocation density devices. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 1505-1510		
58	The electron effective mass at the bottom of the GaNAs conduction band. *Semiconductor Science and Technology*, **2004**, 19, 1189-1195	1.8	19
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